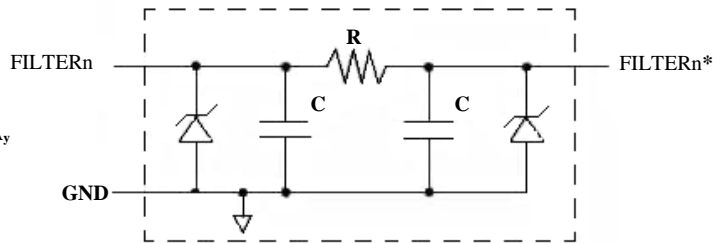
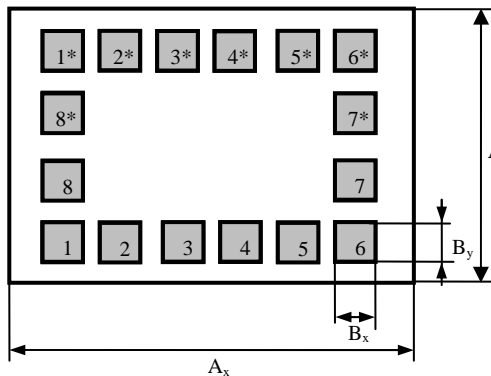


**8 Channel EMI Filter Array with ESD Protection.**


**Mechanical date:**  $A_x = 850\mu\text{m}$ ,  $A_y = 590\mu\text{m}$ .  
 $B_x = B_y = 85\mu\text{m}$

**Schematic and pinning diagram.**

**Chip thickness:**  $138 \pm 12\mu\text{m}$ .

**Scribe Line width** -  $60\mu\text{m}$ .

**Top Metal:** Al – for wire bonding,  $d = 2.2 \pm 0.2\mu\text{m}$ .

**Back side:** Ti-Ni-Ag for soldering.

**Back side – GND**

### Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	$V_{RWM}$	-	5	V
Electrostatic Discharge	$V_{ESD}$	IEC 61000-4-2, level 4	+/-12 (Contact); +/-17 (Air).	kV
Junction temperature	$T_J$	-	125	°C
Operating temperature	$T_{OP}$	-	-40 to +85	°C

### Characteristics ( $T_j = 25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{BR}$	Breakdown voltage	$I_R = 1\text{mA}$	6.02	-	9.0	V
$I_R$	Diode reverse leakage current.	$V = 3\text{V}$	-	-	0.45	$\mu\text{A}$
R	Resistance	-	86	100	114	Ohm
$C_1, C_2$	Capacitance	$V_R = 2.5\text{V}$ , $f = 1\text{MHz}$	8	10	12	pF
$C_{in}$	Capacitance	$V_R = 2.5\text{V}$ , $f = 1\text{MHz}$	16	20	24	pF

\*- For Device testing.